

IGBT Transistor

MG200Q1US41

1200V / 200A

DATASHEET

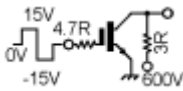
OEM – Toshiba

Source: Toshiba Databook 1995/96

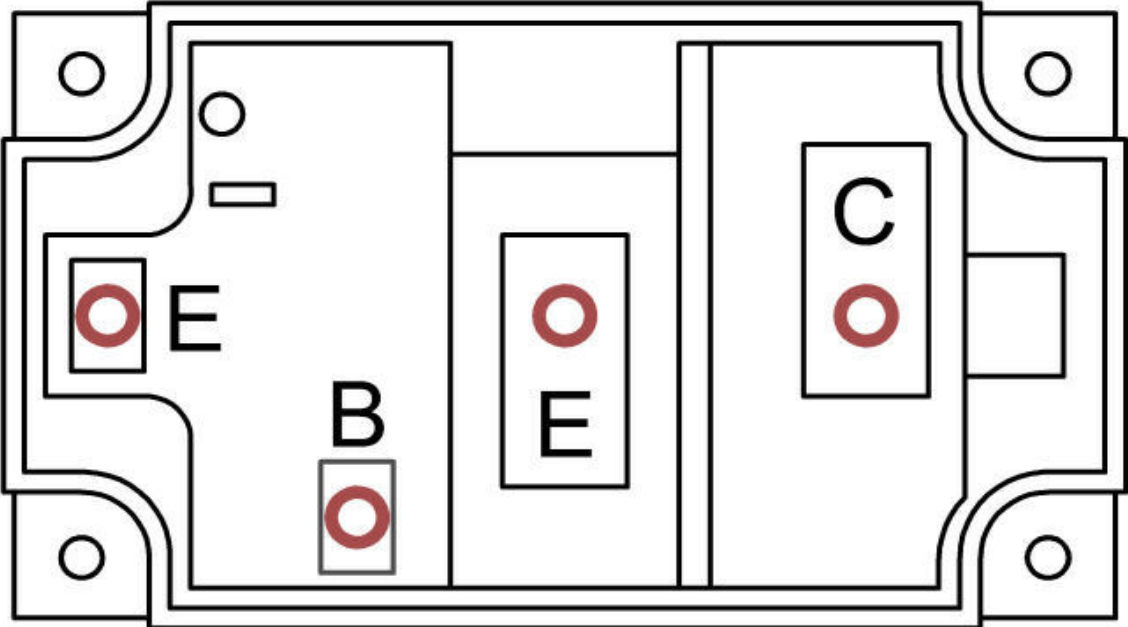
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		Vces	1200	V
Gate-Emitter Voltage		Vges	+/-20	V
Collector Current	DC	IC	200	A
	1ms	Icp	400	A
Forward Current	DC	If	200	A
	1ms	Ifm	400	A
Collector Power Dissipation		Pc	1400	W
Junction Temperature		Tj	150	°C
Storage Temperature Range		Tstg	-40~125	°C
Isolation Voltage		Visol	2500 (AC 1min.)	V
Screw Torque (Terminal / M4 / M6 / Mounting)		-	2/3/3	N*m

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		Iges	Uge=+/-20V, Vce=0	-	-	+40	uA
Collector Cut-off Current		Ices	Uce=1200V, Uge=0	-	-	4.0	mA
Gate-Emitter Cut-off Voltage		Uge (off)	Ic=200mA, Uce=5V	3.0	-	6.0	V
Collector-Emitter Saturation Voltage		Uce (sat)	IC=200A, Uge=15V	-	3.0	4.0	V
Input Capacitance		Cies	Uce=10V, Uge=0, f=1MHz	-	24000	-	pF
Switching Time	Rise Time	tr		-	0.30	0.60	uS
	Turn-on Time	ton		-	0.40	0.80	
	Fall Time	tf		-	0.20	0.50	
	Turn-off Time	toff		-	0.8	1.50	
Forward Voltage		Vf	If=200A, Uge=0	-	2.0	3.0	V
Reverse Recovery Time		trr	If=200A, Uge=-10V di/dt=300A/uS	-	0.25	0.50	uS
Thermal Resistance	Rth (j-c)	Transistor		-	-	0.089	°C/W
		Diode		-	-	0.25	

2-109A4A



EQUIVALENT CIRCUIT

